

**SIEMENS**

**Pulsed Laser Diode in Plastic Package  
10 W Peak (Class 3 Laser Product)**

**SPL PLxx  
(SFH 4884xx)**

**Preliminary**

**Features**

- Low cost plastic package
- Reliable strained InGaAs/GaAs material
- High power large-optical-cavity structure
- Single emitting area  $200 \mu\text{m} \times 2 \mu\text{m}$



**Applications**

- Range finding
- Security, surveillance
- Illumination, ignition
- Testing and measurement

Type	Old Type (as of Oct. 1996)	Wavelength *)	Ordering Code
SPL PL85	SFH 488425	850 nm	Q62702-P1759
SPL PL90	–	904 nm	on request

\*) Other wavelengths in the range of 780 nm ... 980 nm are available on request.

**Maximum Ratings**

( $T_A = 25^\circ\text{C}$ )

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Forward current	$I_F$	–	–	20	A
Pulse width (FWHM)	$t_p$	–	–	100	ns
Duty factor	$D$	–	0.1	–	%
Reverse voltage	$V_R$	–	–	3	V
Operating temperature	$T_{op}$	– 20	...	+ 85	$^\circ\text{C}$
Storage temperature	$T_{stg}$	– 40	...	+ 100	$^\circ\text{C}$
Soldering temperature ( $t_{m,\text{ax}} = 5 \text{ s}$ , 2 mm from bottom edge of case)	$T_s$	–	–	260	$^\circ\text{C}$

**Optical Characteristics**  
( $T_A = 25^\circ\text{C}$ )

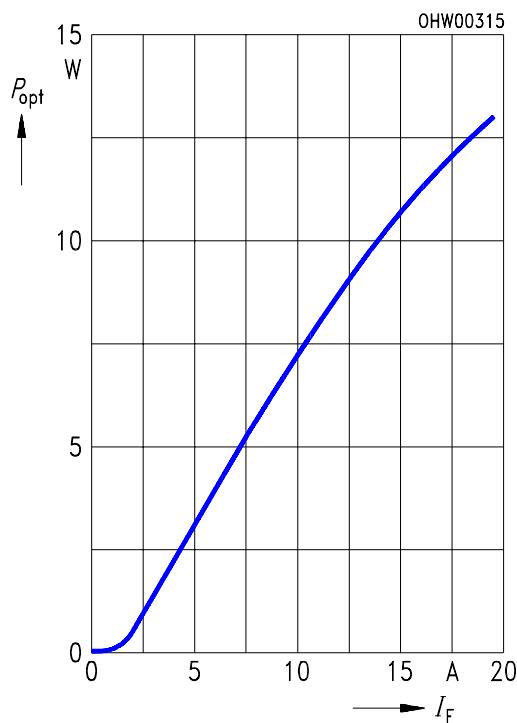
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Emission wavelength <sup>1)</sup>	$\lambda$	830	850	870	nm
Spectral width (FWHM) <sup>1)</sup>	$\Delta\lambda$		4		nm
Forward current (10 W) <sup>1)</sup>	$I_f$	—	—	14	A
Threshold current	$I_{th}$	—	1	—	A
Forward voltage (0.1 A)	$V_F$	—	1.6	—	V
Forward voltage (20 A)	$V_F$	—	6	10	V
Rise and fall time (10% ... 90%)	$t_r, t_f$	2	10	—	ns
Beam spread at 20 A (FWHM)	$\theta_{  } \times \theta_{\perp}$	—	10 × 30	—	°
Temperature coefficient of wavelength <sup>2)</sup>	$\partial\lambda / \partial T$	0.25	0.27	0.30	nm/K
Temperature coefficient of optical power	$\partial P / \partial T$	—	− 0.5	—	%/K
Thermal resistance	$R_{th\ JA}$	—	160	—	K/W

1) Standard operating conditions refer to pulses of 50 ns at 10 kHz rate with 10 W peak power into NA = 0.5

2) Depending on emission wavelength.

## Optical Characteristics ( $T_A = 25^\circ\text{C}$ )

### Radiant Power $P_{\text{cw}}$ vs. $I_F$

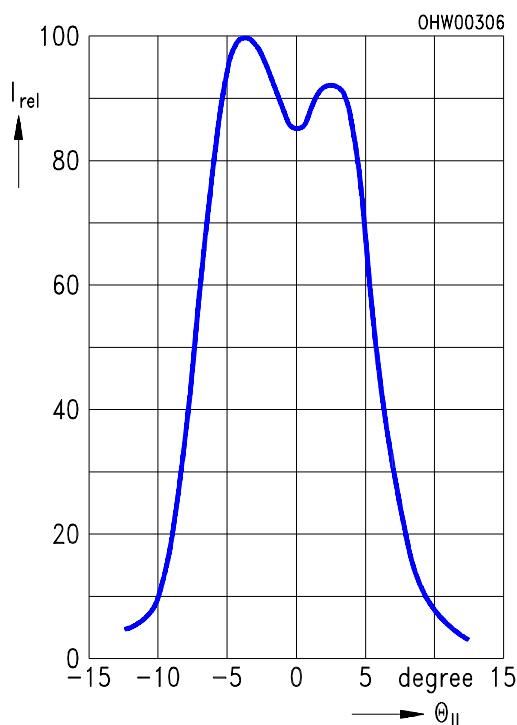


### Permissible pulse handling capability; $I_F$ vs. $t$ ; Parameter D (duty cycle)

Max. forward current vs pulse length  $I_F$  vs.  $\tau$ ; parameter D duty cycle is under evaluation

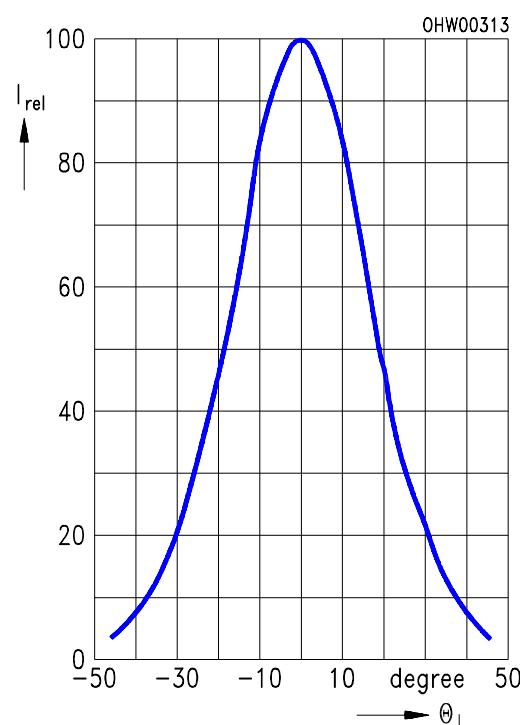
### Farfield Distribution

#### Parallel to Junction $I_{\text{rel}}$ vs. $\theta_{\parallel}$



### Farfield Distribution

#### Parallel to Junction $I_{\text{rel}}$ vs. $\theta_{\perp}$



**Package Outlines**

(Dimensions in mm, unless specified)

